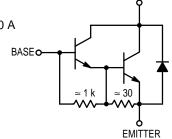
NPN Silicon Darlington Power Transistor

The BU323AP is a monolithic darlington transistor designed for automotive ignition, switching regulator and motor control applications.

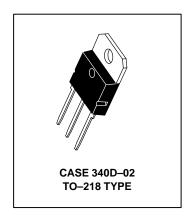
- Collector–Emitter Sustaining Voltage VCER(sus) = 475 Vdc
- 125 Watts Capability at 50 Volts
- V_{CE} Sat Specified at −40°C = 2.0 V Max. at I_C = 6.0 A
- Photoglass Passivation for Reliability and Stability



COLLECTOR

BU323AP

DARLINGTON NPN SILICON POWER TRANSISTOR 400 VOLTS 125 WATTS



MAXIMUM RATINGS

Rating	Symbol	Value	Unit	
Collector–Emitter Voltage	VCEO(sus)	400	Vdc	
Collector–Emitter Voltage	V _{CEV}	475	Vdc	
Emitter–Base Voltage	V _{EB}	6.0	Vdc	
Collector Current — Continuous — Peak (1)	I _C	10 16	Adc	
Base Current — Continuous — Peak (1)	I _B I _{BM}	3.0	Adc	
Total Power Dissipation — $T_C = 25^{\circ}C$ — $T_C = 100^{\circ}C$ Derate above 25°C	PD	125 100 1.0	Watts Watts W/°C	
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200	°C	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	1.0	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	TL	275	°C

(1) Pulse Test: Pulse Width = 5.0 ms, Duty Cycle ≤ 10%.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS ¹			•		•
Collector–Emitter Sustaining Voltage (Figure 1) L = 10 mH (IC = 200 mAdc, IB = 0, V _{Clamp} = Rated V _{CEO})	VCEO(sus)	400			Vdc
Collector–Emitter Sustaining Voltage (Figure 1) (I _C = 3 A, R _{BE} = 100 Ohms, L = 500 μH) Unclamped	VCER(sus)				Vdc
Collector Cutoff Current (Rated V _{CER} , R _{BE} = 100 Ohms)	lass	475	1	1	mAdc
Collector Cutoff Current (Rated VCBO, IE = 0)	ICER			1	mAdc
Emitter Cutoff Current (V _{EB} = 6 Vdc, I _C = 0)	l _{CBO}			40	mAdc
ON CHARACTERISTICS ¹	l _{EBO}			40	MAGC
DC Current Gain (I _C = 3 Adc, V _{CE} = 6 Vdc) (I _C = 6 Adc, V _{CE} = 6 Vdc) (I _C = 10 Adc, V _{CE} = 6 Vdc)	hFE	300 150 50	550 350 150	2000	
Collector–Emitter Saturation Voltage (I _C = 3 Adc, I _B = 60 mAdc) (I _C = 6 Adc, I _B = 120 mAdc) (I _C = 10 Adc, I _B = 300 mAdc) (I _C = 6 Adc, I _B = 120 mAdc, T _C = -40°C)	VCE(sat)			1.5 1.7 2.7 2.0	Vdc
Base–Emitter Saturation Voltage ($I_C = 6$ Adc, $I_B = 120$ mAdc) ($I_C = 10$ Adc, $I_B = 300$ mAdc) ($I_C = 6$ Adc, $I_B = 120$ mAdc, $I_C = -40$ °C)	VBE(sat)			2.2 3 2.4	Vdc
Base–Emitter On Voltage (I _C = 10 Adc, V _{CE} = 6 Vdc)	V _{BE(on)}			2.5	Vdc
Diode Forward Voltage (I _F = 10 Adc)	V _f		2	3.5	Vdc
DYNAMIC CHARACTERISTICS					
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f _{test} = 100 kHz)	C _{ob}		165	350	pF
SWITCHING CHARACTERISTICS					
Storage Time $(V_{CC} = 12 \text{ Vdc}, I_{C} = 6 \text{ Adc},$	t _S		7.5	15	μs
Fall Time	t _f		5.2	15	μs
FUNCTIONAL TESTS	•				•
Second Breakdown Collector Current with Base–Forward Biased	I _{S/B}		See Figure 10		
Pulsed Energy Test (See Figure 12)	I _C 2 _L /2	550			mJ

¹Pulse Test: Pulse Width = 300 μ s, Duty Cycle = 2%.

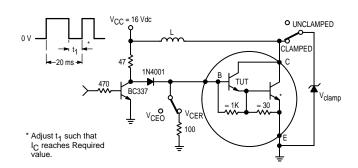


Figure 1. Sustaining Voltage Test Circuit

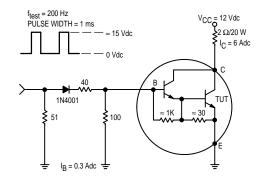


Figure 2. Switching Times Test Circuit

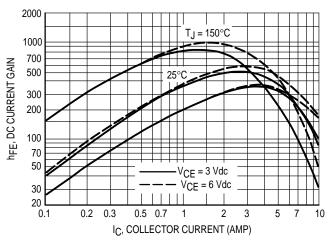


Figure 3. DC Current Gain

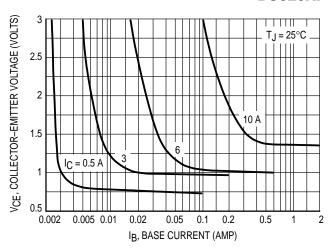


Figure 4. Collector Saturation Region

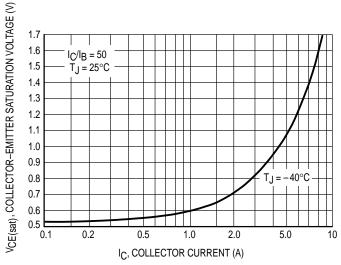


Figure 5. Collector-Emitter Saturation Voltage

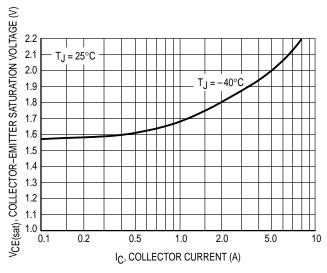


Figure 6. Base-Emitter Voltage

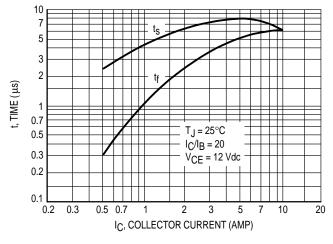


Figure 7. Turn-Off Switching Time

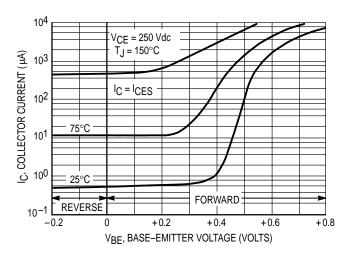


Figure 8. Collector Cutoff Region

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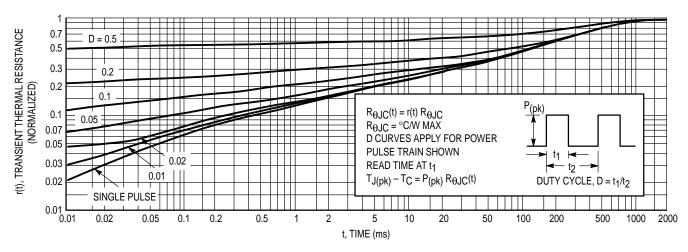


Figure 9. Thermal Response

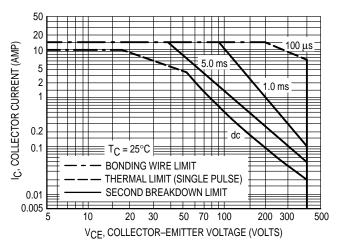


Figure 10. Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor average junction temperature and second breakdown. Safe operating area curves indicate $I_{\text{C}} - V_{\text{CE}}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 10 is based on $T_C=25\,^{\circ}C$, $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated when $T_C \ge 25\,^{\circ}C$. Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown on Figure 10 may be found at any case temperature by using the appropriate curve on Figure 11.

 $T_{J(pk)}$ may be calculated from the data in Figure 11. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

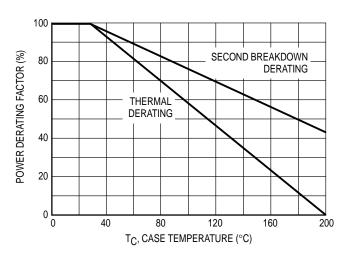
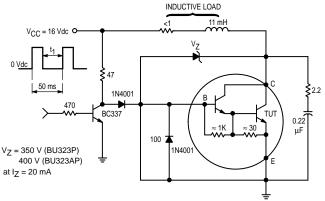


Figure 11. Power Derating

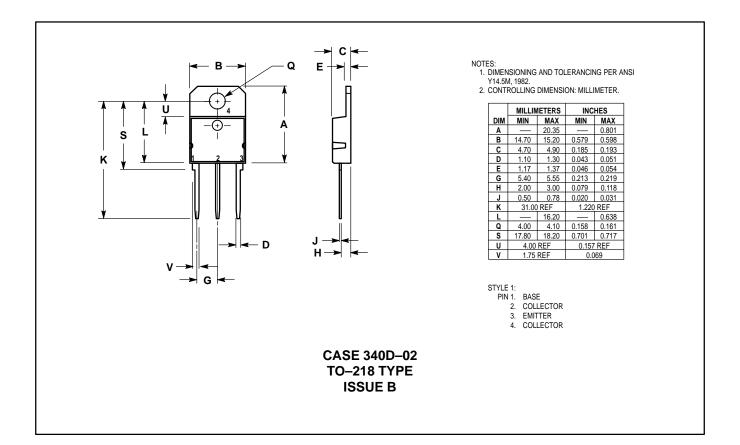


t₁ to be selected such that I_C reaches 10 Adc before switch-off.

NOTE: Figure 12 specifies energy handling capabilities in an automotive ignition circuit.

Figure 12. Ignition Test Circuit

PACKAGE DIMENSIONS



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